

wherein a surface zone of the first conductivity type ~~is~~
~~formed-forming~~forms ~~one of the~~ first anode and cathode zones
area of the SCR element, and

the surface area ~~having~~has a surface zone of the second
conductivity type, further denoted as first zone, situated
remote from the well and forming the ~~other~~ a second anode and
cathode area of the SCR element, and

the gated diode containing a gate insulated from the
surface of the semiconductor body and a highly-doped second
conductivity type surface zone aligned to this gate further
denoted as second zone, which aligned surface zone partly
overlaps the well of the second conductivity type, characterized
in that the said second zone stretches out only along a part of
the periphery of the well, whereas the first zone is provided
along at least another part of this periphery of the well which
is free from the said second zone.

4. (Amended) A semiconductor device as claimed in claim 3,
characterized in that the ~~said~~ further zone of the second
conductivity type and the said first zone of the second
conductivity type form a coherent ~~zone~~ of the second
conductivity type.